

Features of light to current transformations in organic devices

Jean-Michel Nunzi

Physics and Chemistry Departments, Queen's University, Canada

Photovoltaic effect

Auger Fountain electroluminescence



Polymer screens

*Seiko-Epson / CDT
June 2000*



2001



KODAK



2004

Dupont / Uniax, US



Sanyo, Japan



Toshiba, Japan



Siemens, Germany



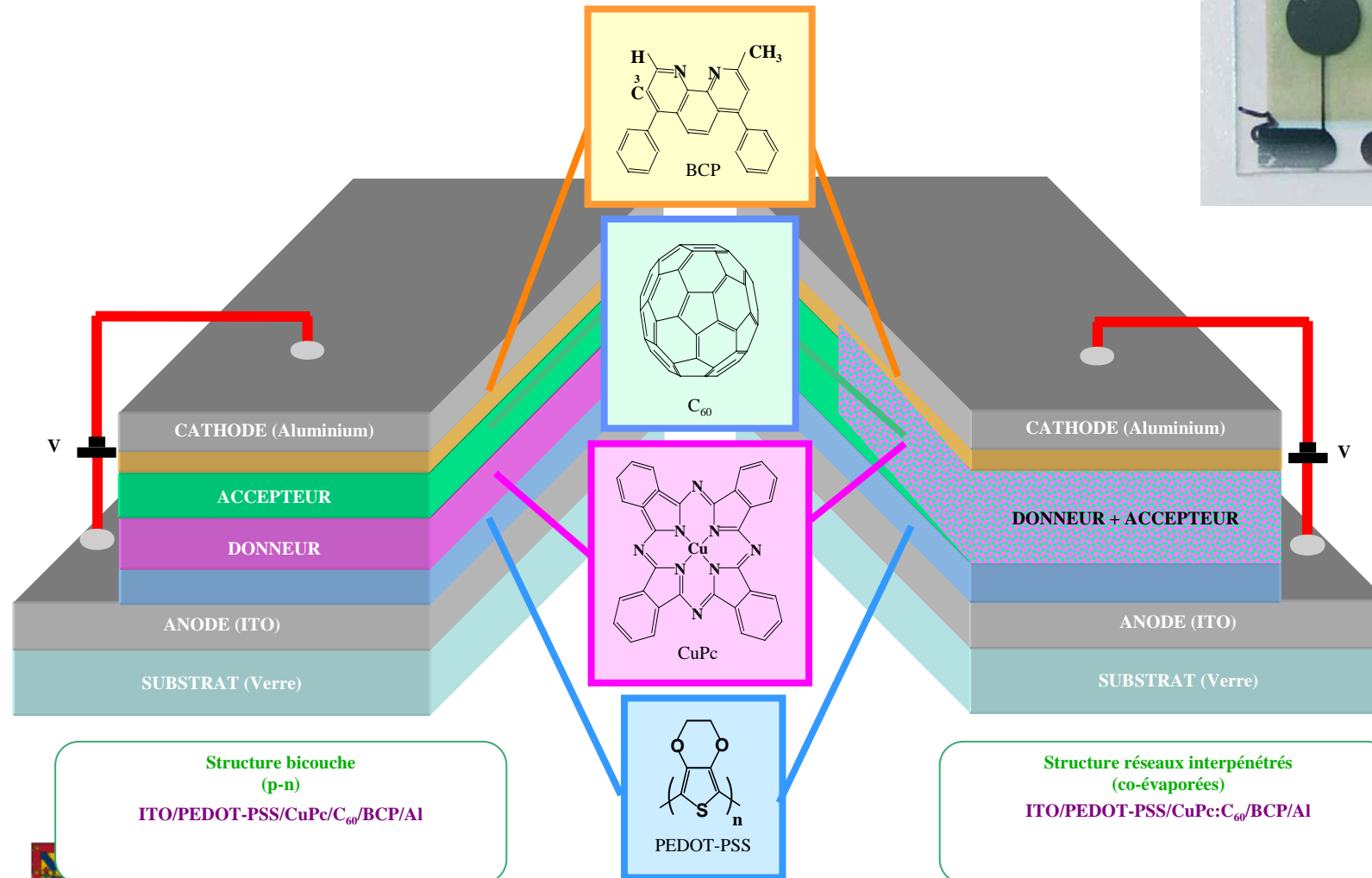
COVION, Germany



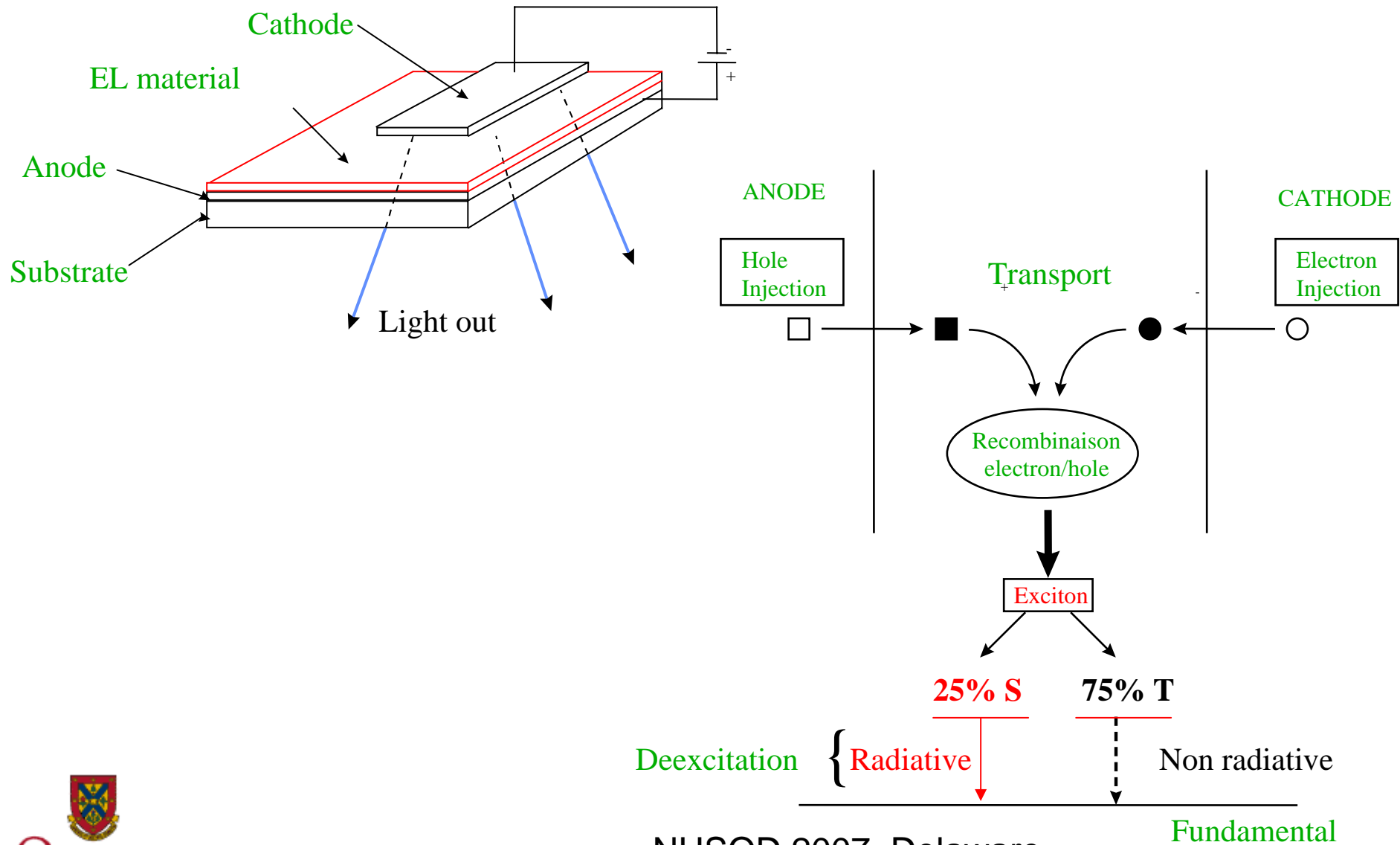
DEL polymère sur substrat souple

Device structure

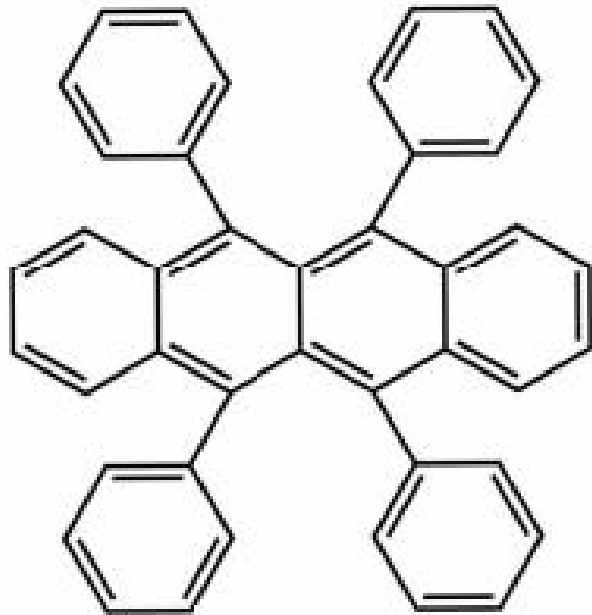
Interfaces and junction



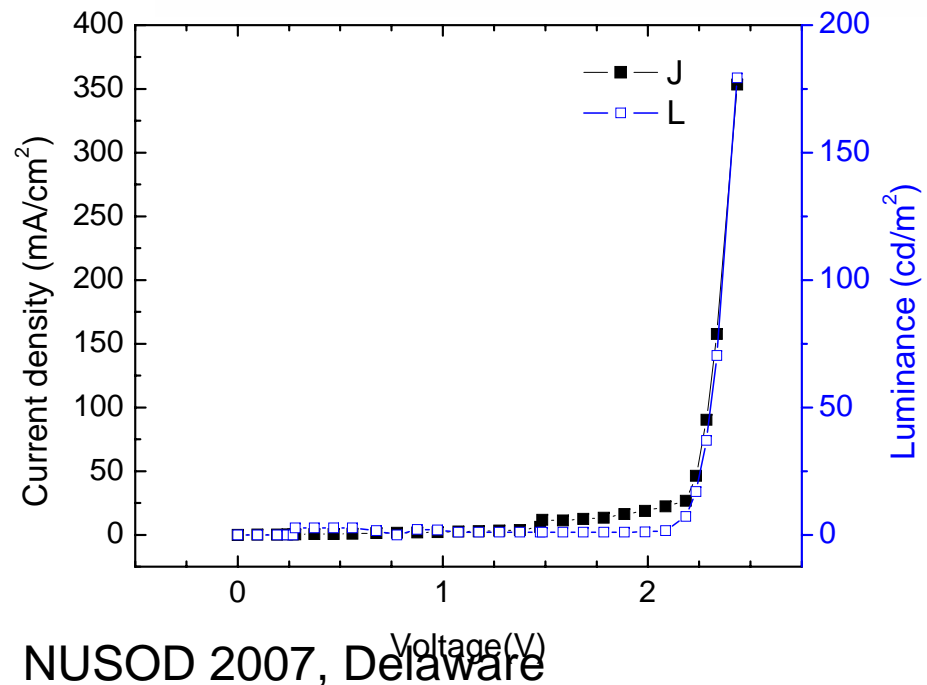
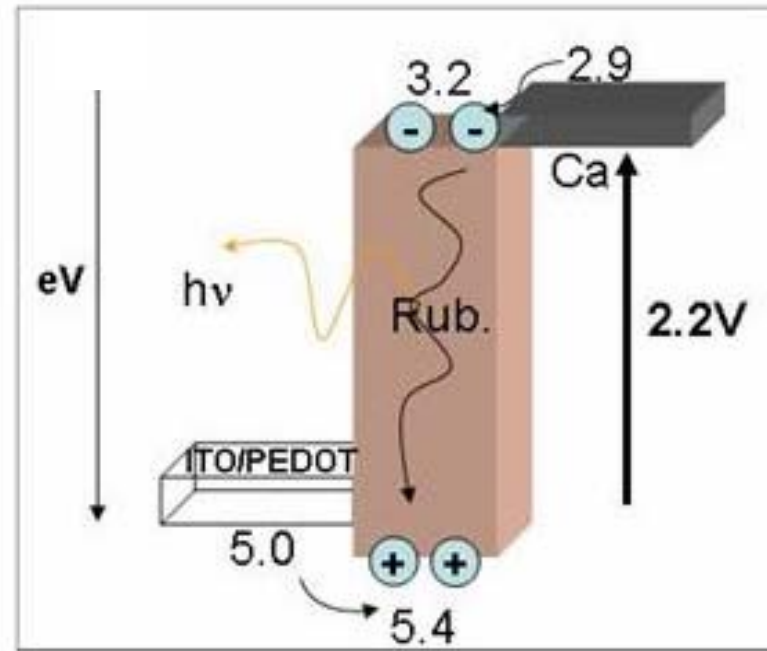
Working principles



Rubrene LED

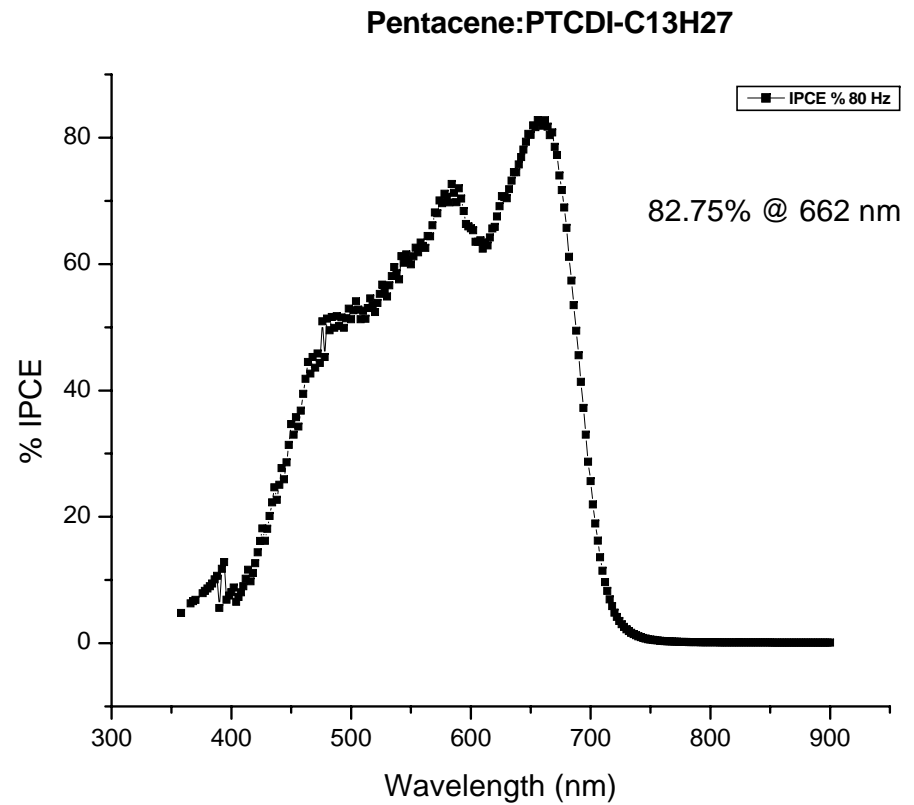
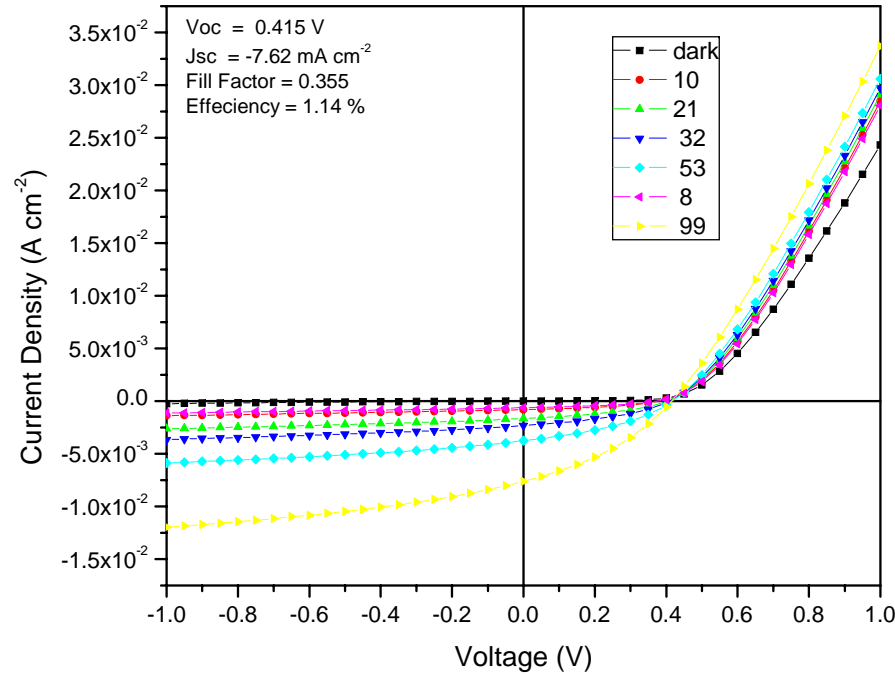


Low-threshold EL



Pac:PTCDI cell - about 2% eff

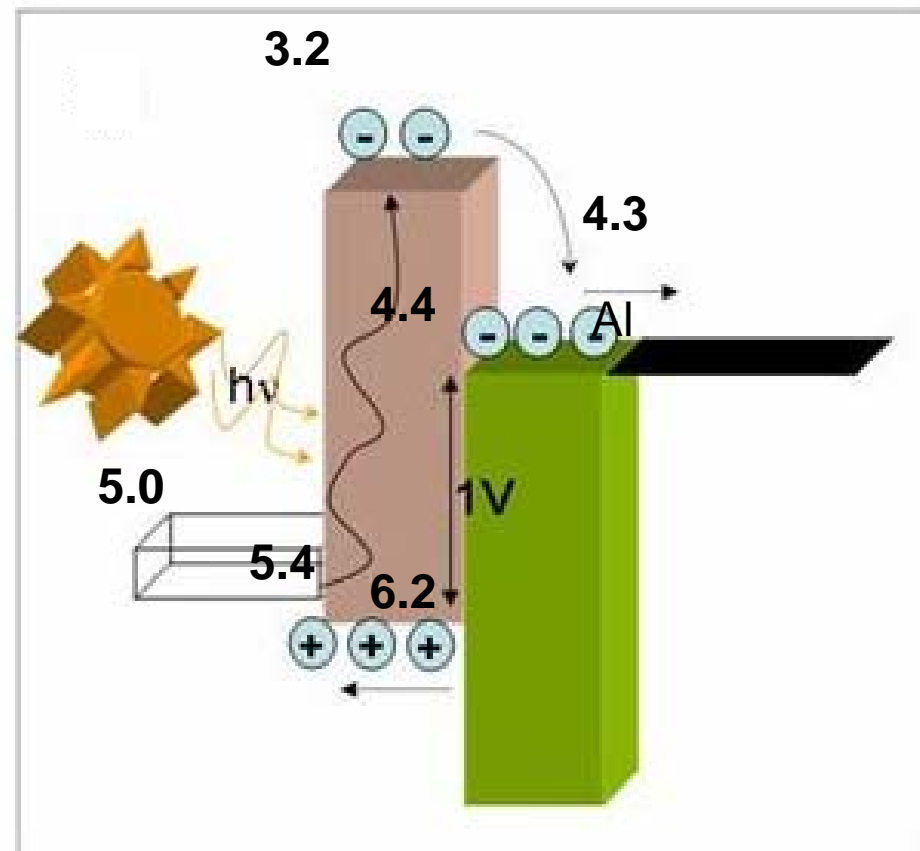
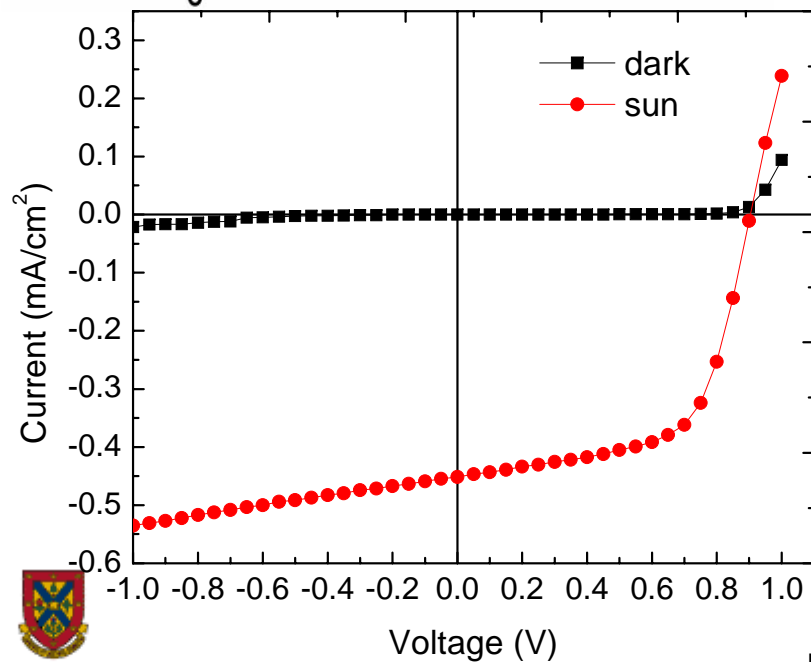
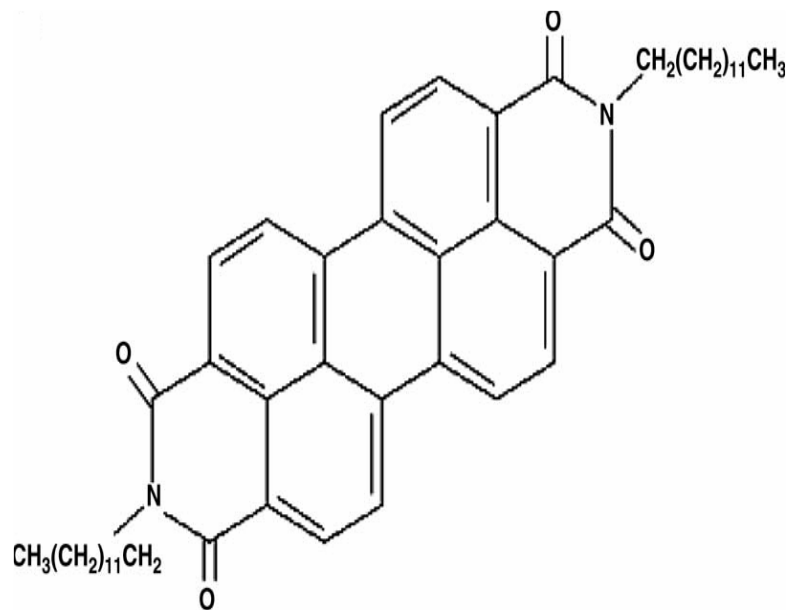
ITO/PEDOT/PENTACENE:PTCDI-C₁₃H₂₇ 100 nm/BCP/Ag : in dark and under illumination (mW cm⁻²)



APL 89, 113506, 2006

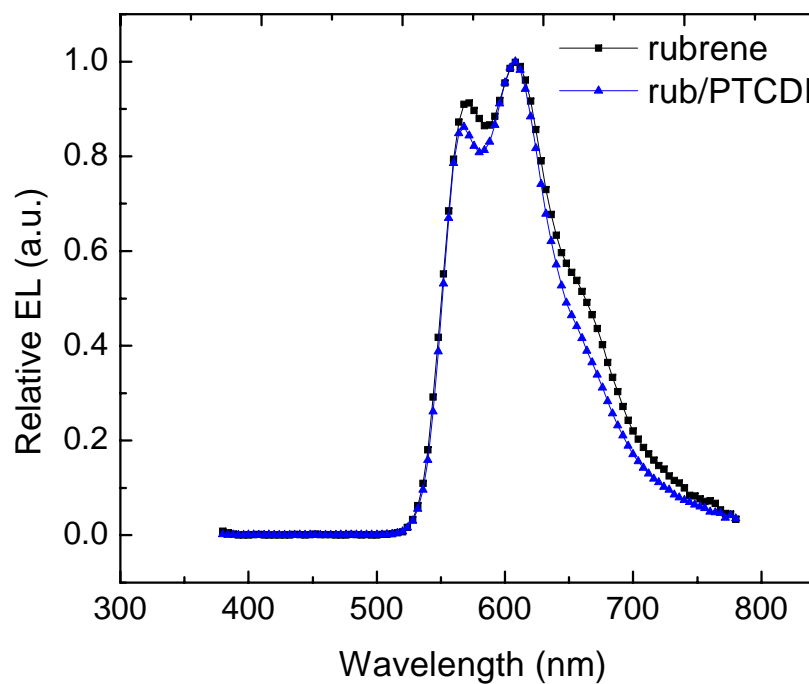
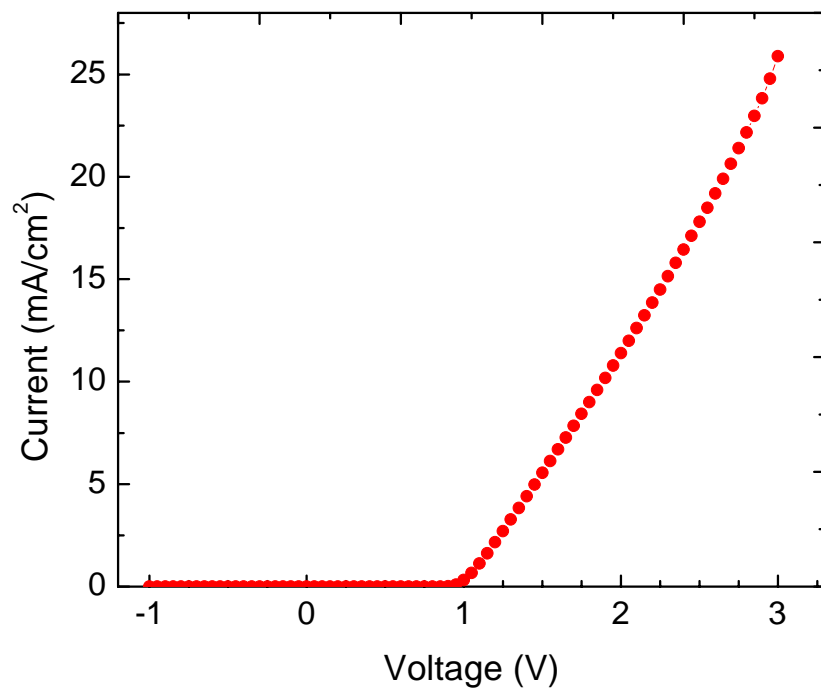


Rubrene / PDI solar cell



Large V_{oc} PV cell

Rubrene / PDI solar cell in dark under higher fw bias



**Same light as Rubrene LED
But injection and EL start at 1V!**

New up-conversion mechanism?

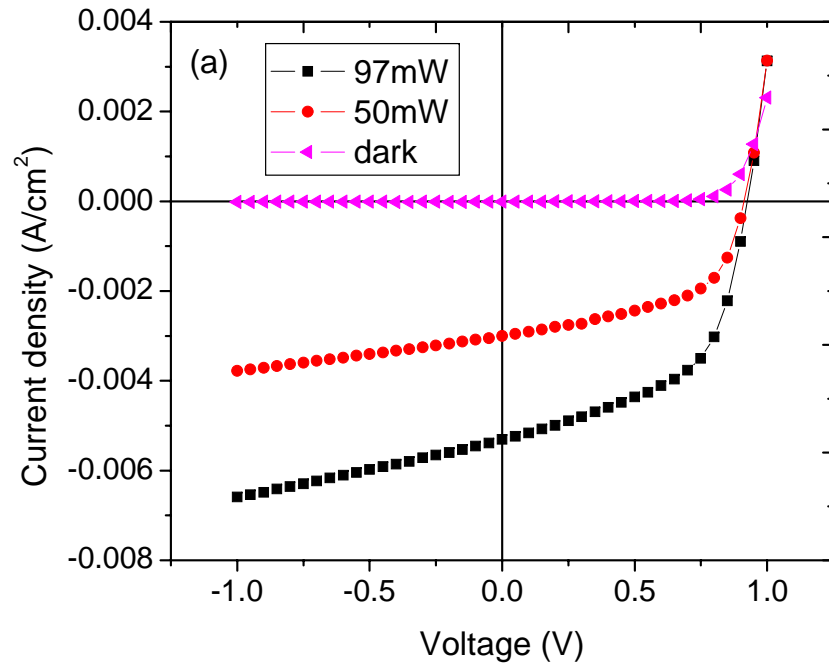
Ajay Pandey, Appl. Phys. Lett. (2007)



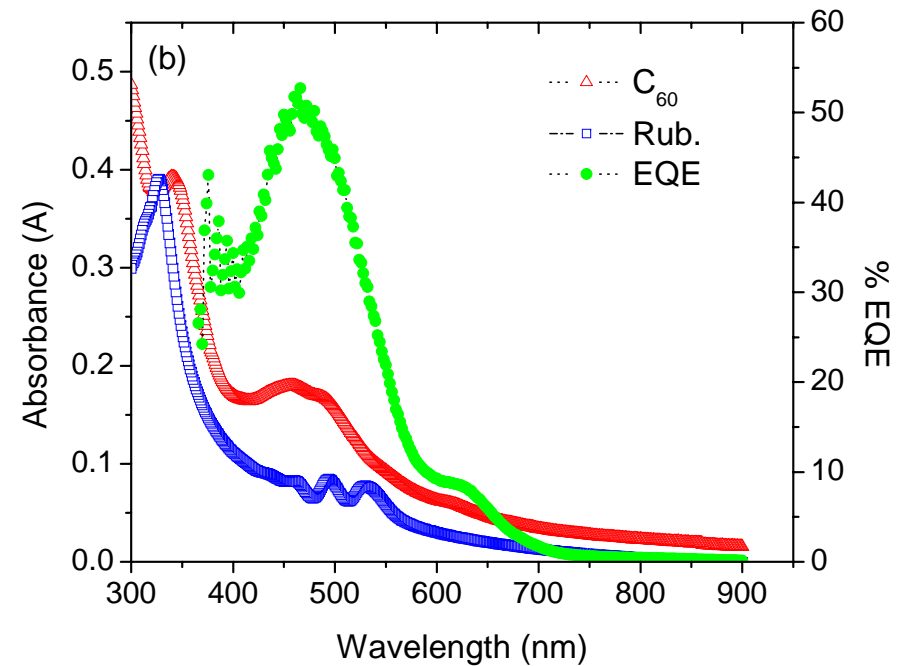
NUSOD 2007, Delaware



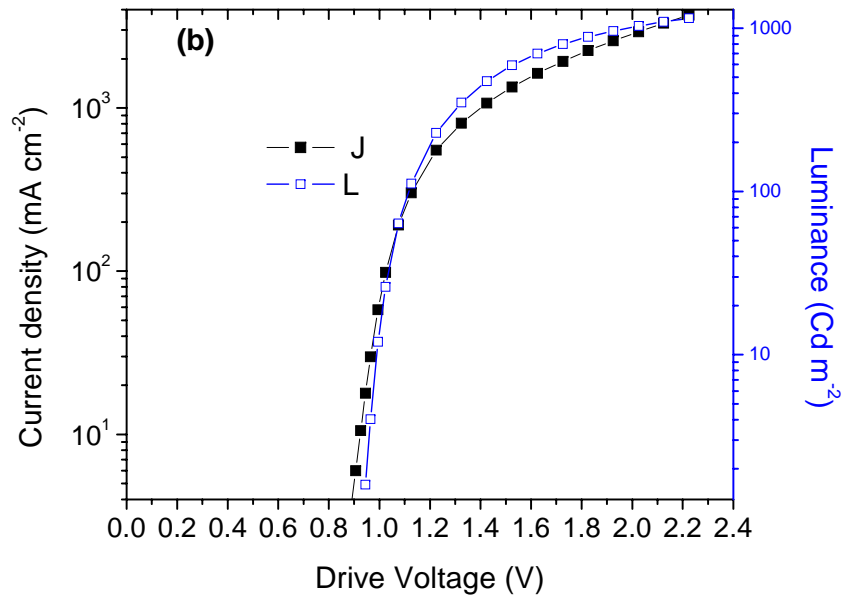
Rubrene / C₆₀ device



Good PV features (2.9% AM 1.5)



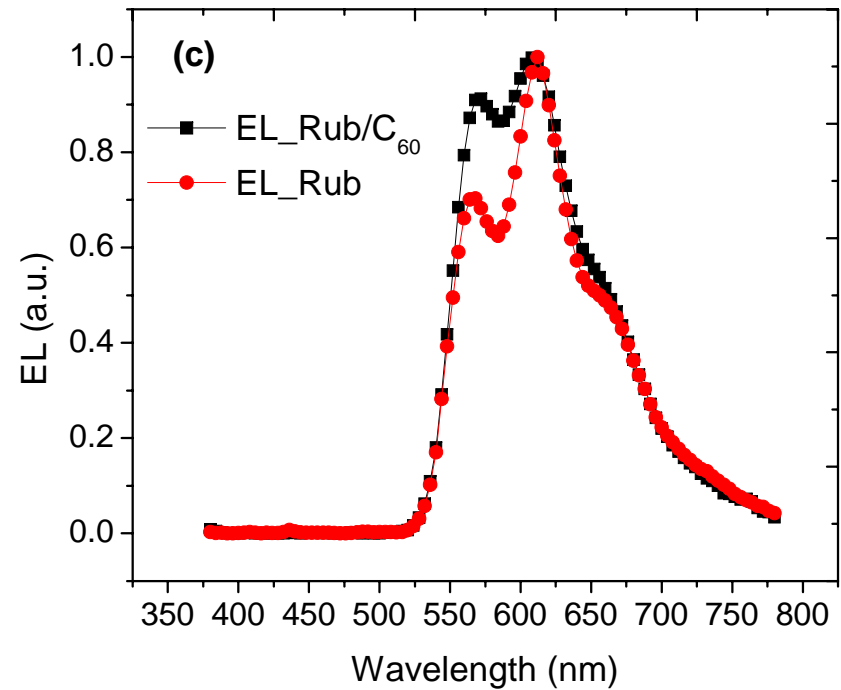
Rubrene / C60 device



Amazing EL feature:

EL threshold \approx PV V_{OC}

Adv. Mater – in press



Auger fountain up-conversion mechanism in heterostructures

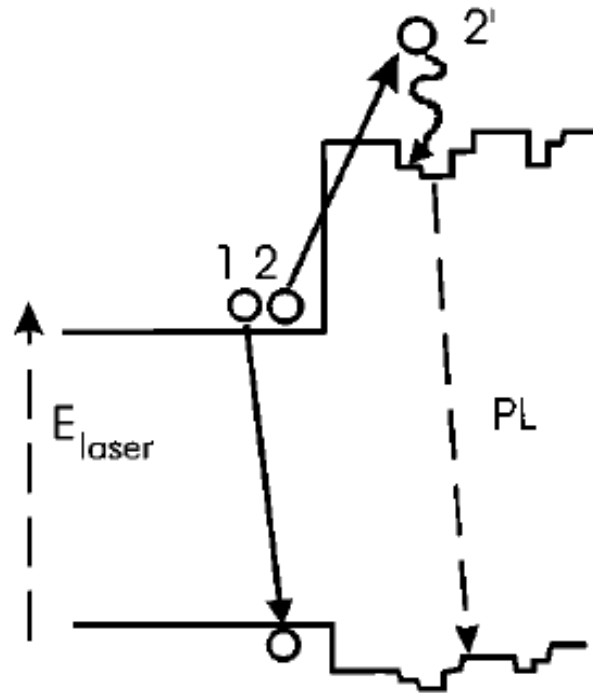
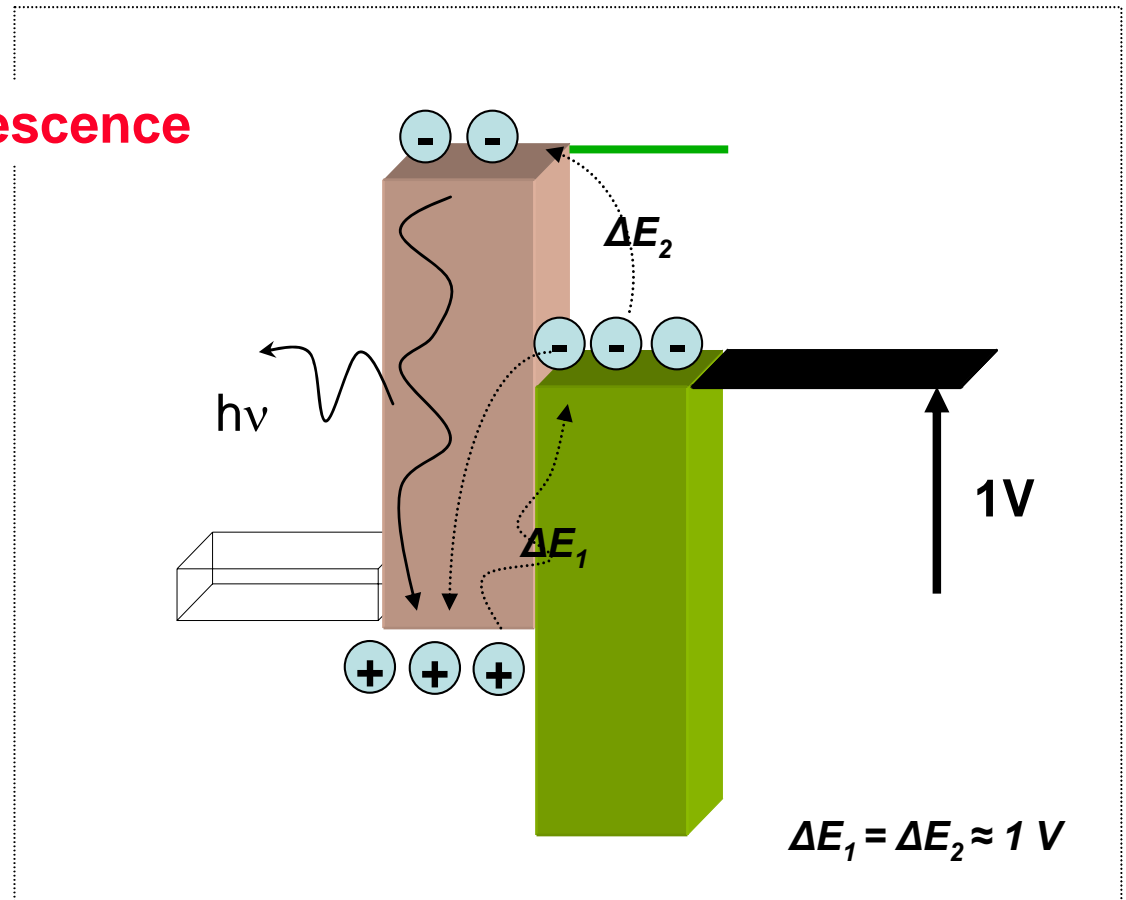


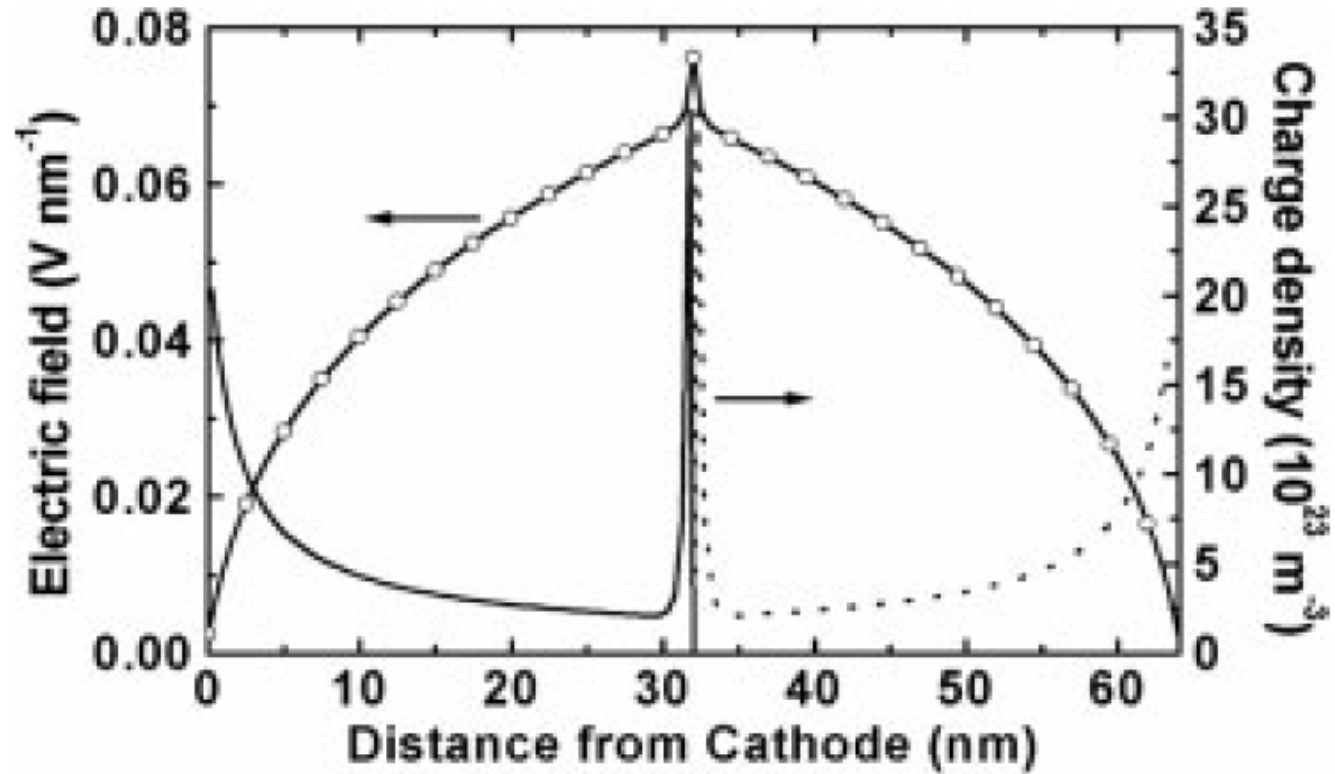
FIG. 2. Sketch of the cold Auger process at the GaAs/ GaInP₂ interface, carrier cooling and trapping, and PL from the GaInP₂ with its composite structure.

Auger fountain electroluminescence



- Charges of both signs accumulate at the interface under 1V-bias
- (-) from C_{60} recombine with (+) from rubrene, exciting CT interface states
- Energy stored at the interface is subsequently transferred to an electron in C_{60}
- Electron is resonantly excited up to the LUMO of rubrene
- Electron recombines radiatively with a hole in the rubrene layer

Charge density & E-field



A.C. Morteani et al., *Adv. Mater.* 2003, 15, 1708

Current density $j = n.q.\mu.E$ across the device is a constant

No net charges cross:

rate of bimolecular recombination per unit surface is exactly $B = j/q$.

Rate R of electron up-conversion to the LUMO of rubrene estimated as:

B times cross section σ of the energy exchange

\times life-time τ of exciplex

\times flux on electrons to interface j/q .

That is $R \approx B.\sigma\tau.j/q$.

External quantum efficiency η_{EQE} of up-converted EL is

$$\eta_{EQE} \approx R. \eta_{EL} / (j/q) = B.\sigma\tau\eta_{EL}$$

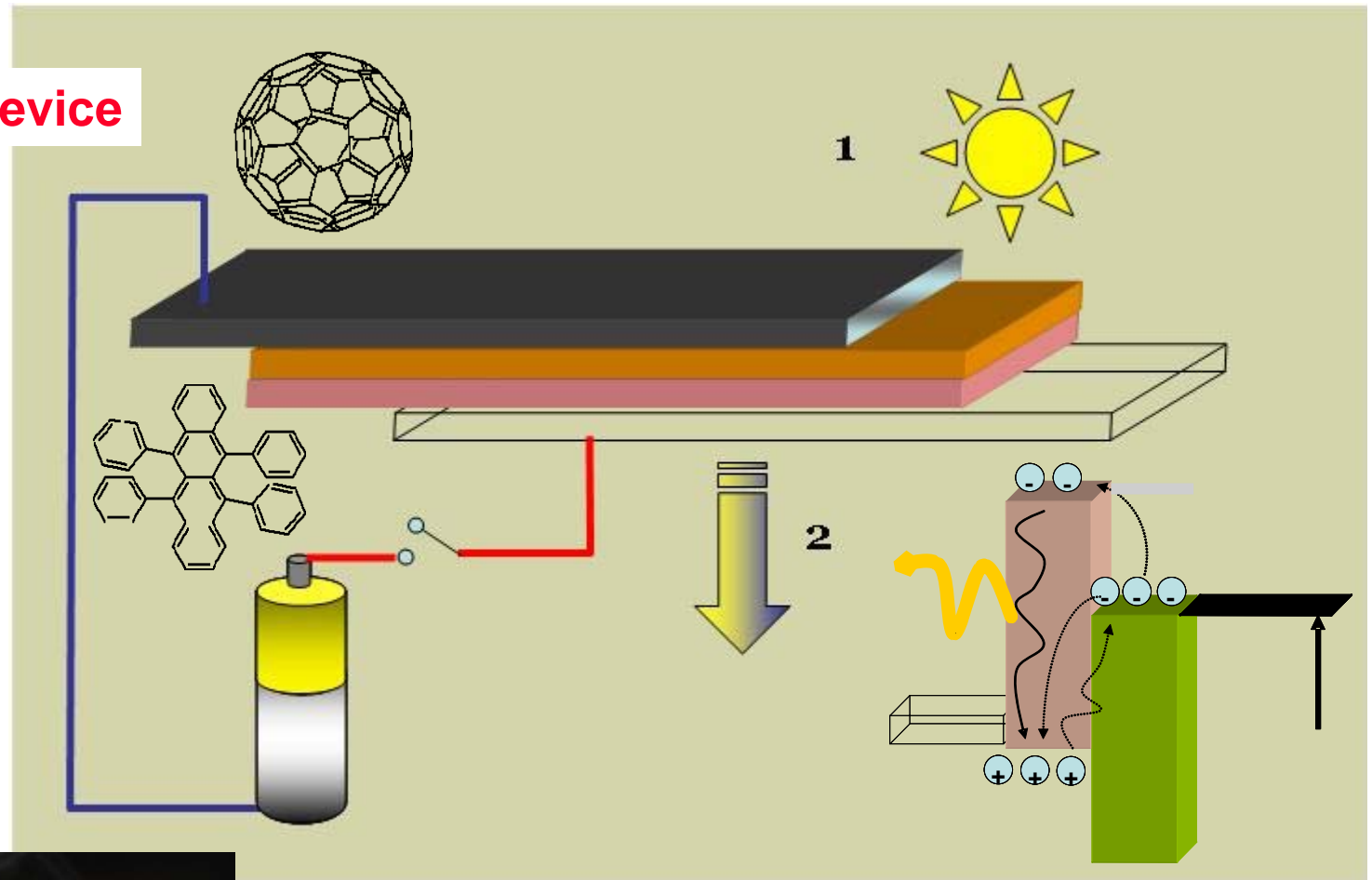
We find experimentally $\eta_{EQE} = 10^{-4}$ when $j = 1 \text{ A/cm}^2$.

$\eta_{EL} = 10^{-2}$, is external coupling efficiency rubrene thin film

We finally get CT exciplex $\sigma\tau \approx 1.6 \cdot 10^{-21} \text{ cm}^2\text{s}$ and $\sigma = 10^{-14} \text{ cm}^2$

That yields $\tau \approx 10^{-7} \text{ s}$

Organic Dual Device



Organic materials can be tailored to achieve better functionalities

**Acknowledgments: U-Angers, ANR, EC
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